

1. US 3695848 B 1972.10.03
2. J. Kim, F. Ren, B. P. Gila, C. R. Abernathy and S. J. Pearton, Reversible barrier height changes in hydrogen-sensitive Pd/GaN and Pt/GaN diodes. *Appl. Phys. Lett.*, 82, Issue 5, 2003, p. 739-741
3. A. El. Kouche, J. Lin, M. E. Law, S. Kim, B. S. Kim, F. Ren and S. J. Pearton, Remote sensing system for hydrogen using GaN Schottky diodes. *Sensors and Actuators, B* 105, Issue 2, 2005, p. 329-333